



注 1) 特記外の抵抗は全てΩおよび1/4Wを示し、容量はpFを示す。
 2) *印は調整用部品を示す。
 NOTES 1. UNLESS OTHERWISE INDICATED RESISTANCES ARE IN OHMS CAPACITANCES ARE IN MICRO-MICRO FRADS.
 2. * VALUES SELECTED IN MANUFACTURE.

付図 1
 NDH-518
 メモリユニット接続図
 MEMORY UNIT SCHEMATIC DIAGRAM
 MODIFICATIONS TO MAKE IT
 SUITABLE FOR THE ADDITIONS

Up/down interface
 or GAL chip
 via IC15 socket
 Original IC15 removed
 With wire-wrap:
 A6 to pin 13
 A7 to pin 16

More stable switch-over and
 suppressing oscillations by
 adding more hysteresis and
 reducing the AC gain

Add BIN → BCD decoding GAL here